

ABSTRACT OF THE DISCLOSURE

A compound semiconductor switching device is based on a designing guideline that isolation should be assured by reducing the gate width of switching FET, thereby
5 reducing the capacitance of the FET. Proper isolation between the two signal passes IS obtained with a FET gate width of about 700 μ m or smaller at a signal frequency of about 2.4 GHz or higher, without employing a shunt FET.

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